



Bipolar NPN Bare Die – BTN192

Part Description

The BTN192 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = 60V
- VCEO = 30V
- VEBO = 5V
- hFE = 100-300 @ VCE = 10V, IC = 0.15A
- VCE(Sat) = 1.6V @ IC = 0.5A, IB = 50mA
- fT = 250 MHz @ VCE = 20V, IE = 0A
- COBO = 8pF @ VCB = 10V

Features

Low VCE(sat)

Die Size (Unawn)

420µm X 420µm, 17 Mils X 17 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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